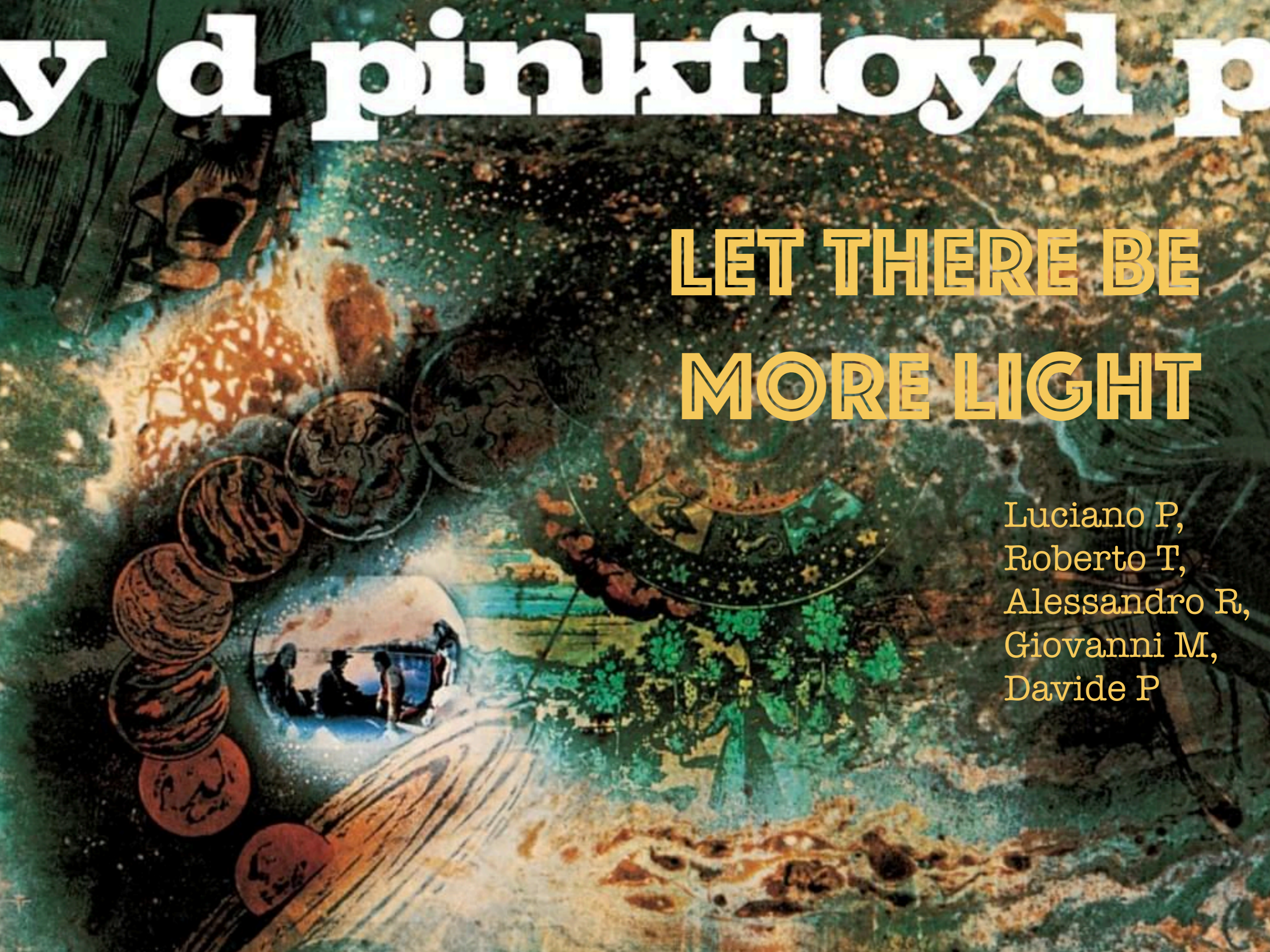


y d pin Floyd p

LET THERE BE MORE LIGHT

Luciano P,
Roberto T,
Alessandro R,
Giovanni M,
Davide P



New Measurements

We started to use LEMON with a mesh 3 mm away from the GEM#3;

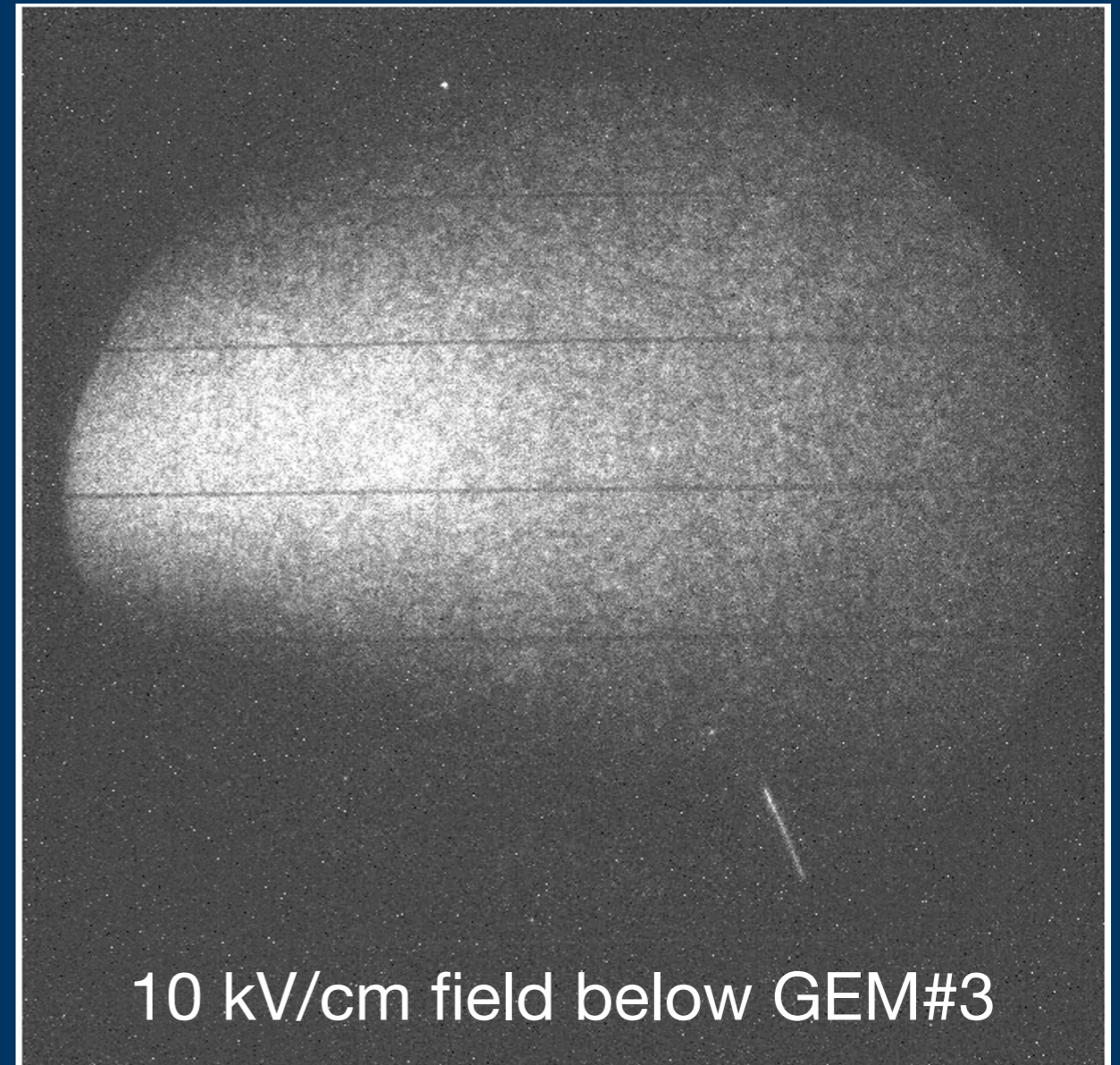
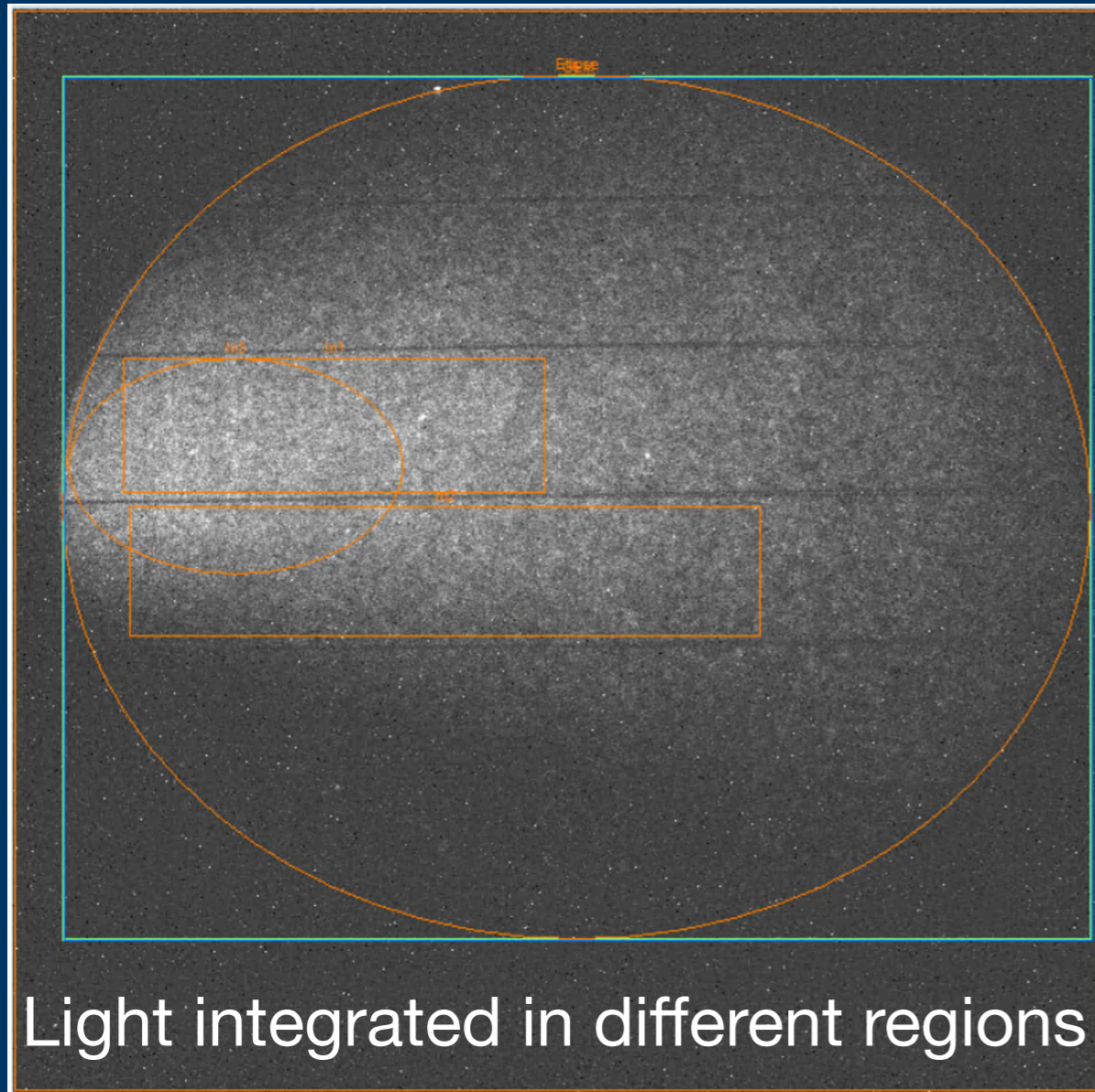
CAEN-HVGEM (A1515TG), allows to acquire the current provided to each channel;

Anode (not used) is grounded as a reference for the HVGEM;

We are using the IMonDet values: leakage currents are automatically subtracted and only signal ones are provided;

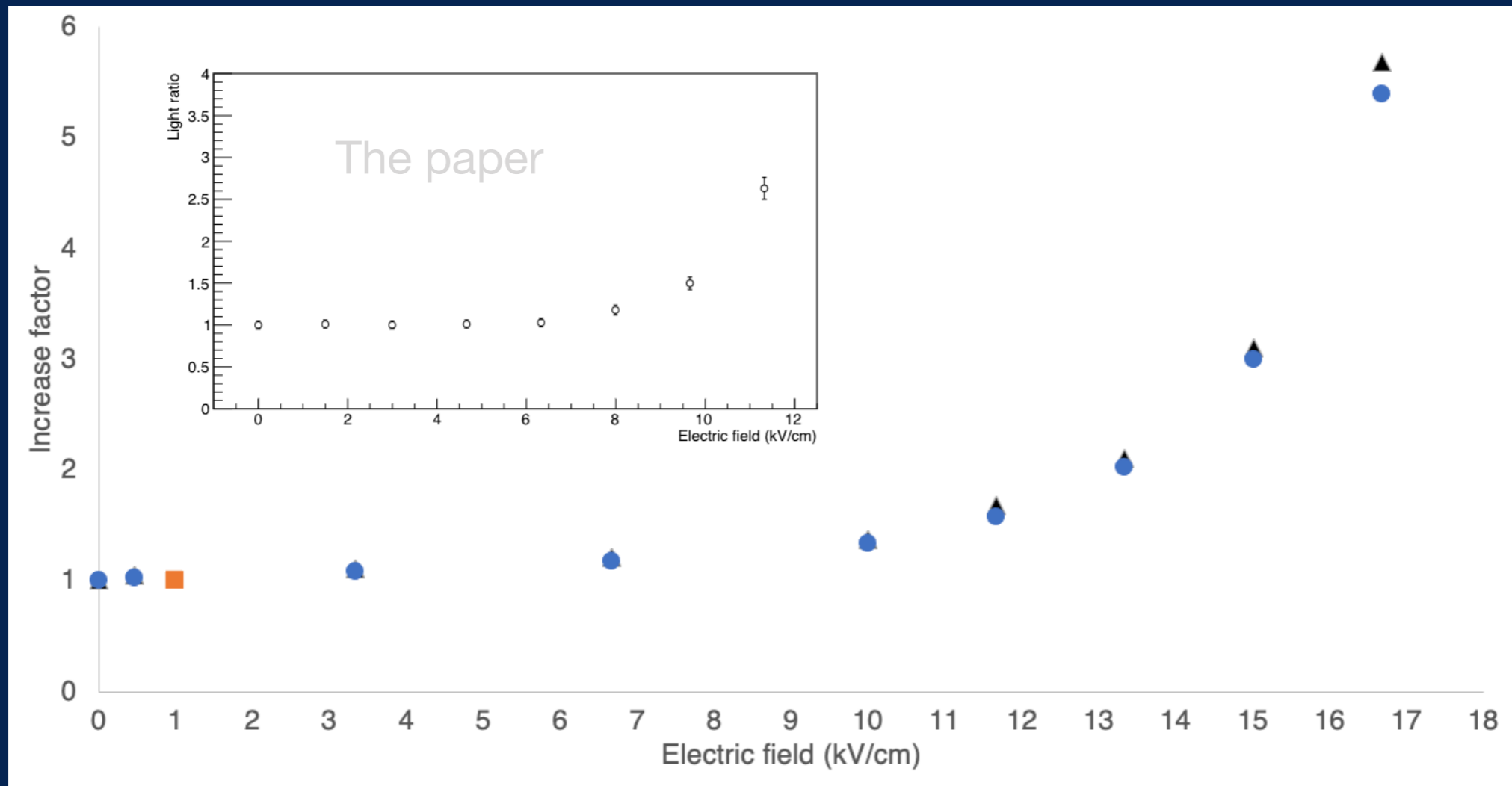
The current drawn by the Mesh is acquired by reading the ΔV across a 10 M Ω resistor;

New test at LNF



- The mesh screens more than 55% of light, spoils image reconstruction;
- Mesh issues solved:
 - Fine up to 5kV;
 - Very good flatness;

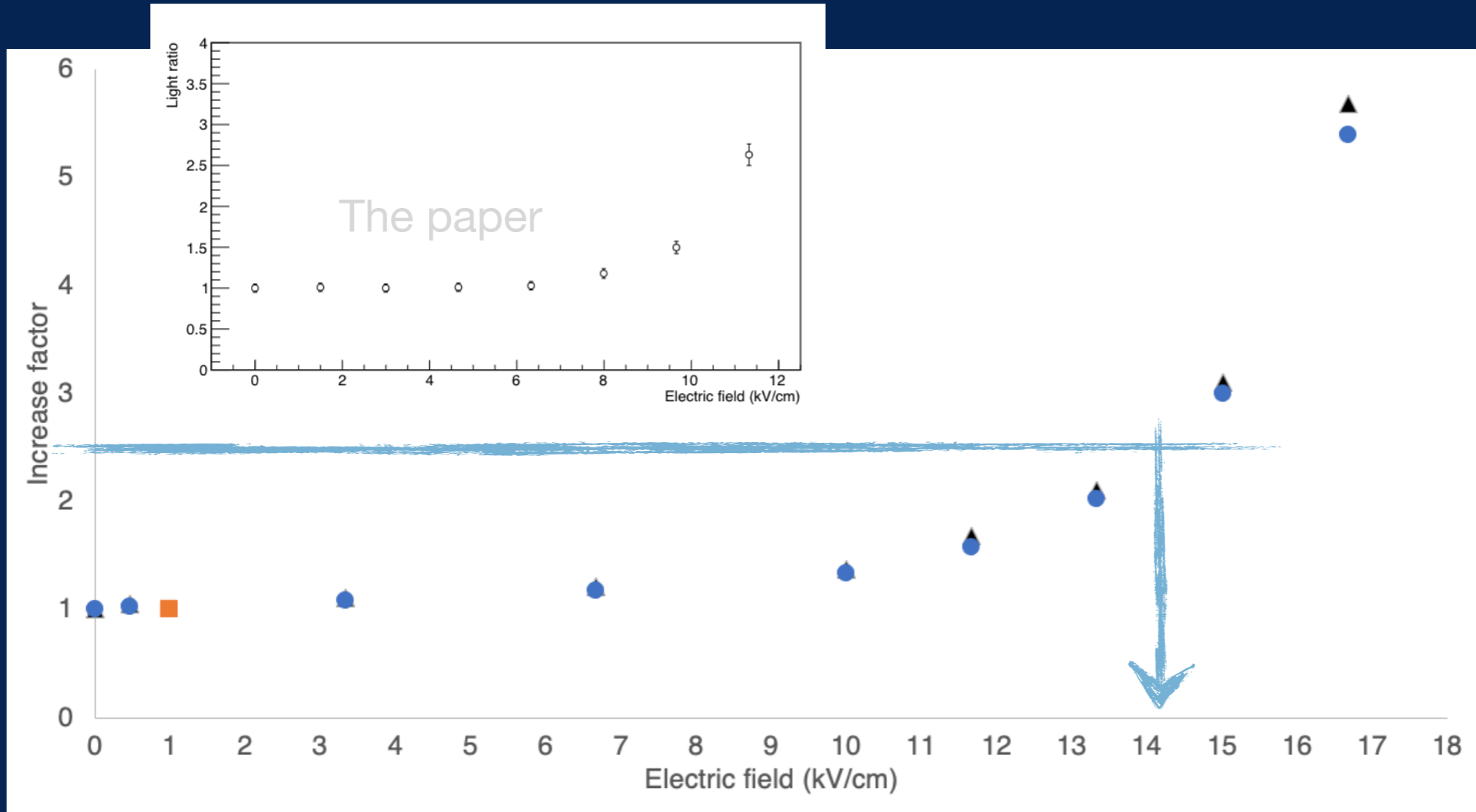
The light



Light is measured in different regions: all measurements in good agreement;

Thanks to the very good quality of the mesh, we E_h explored up to value of almost 17 kV/cm

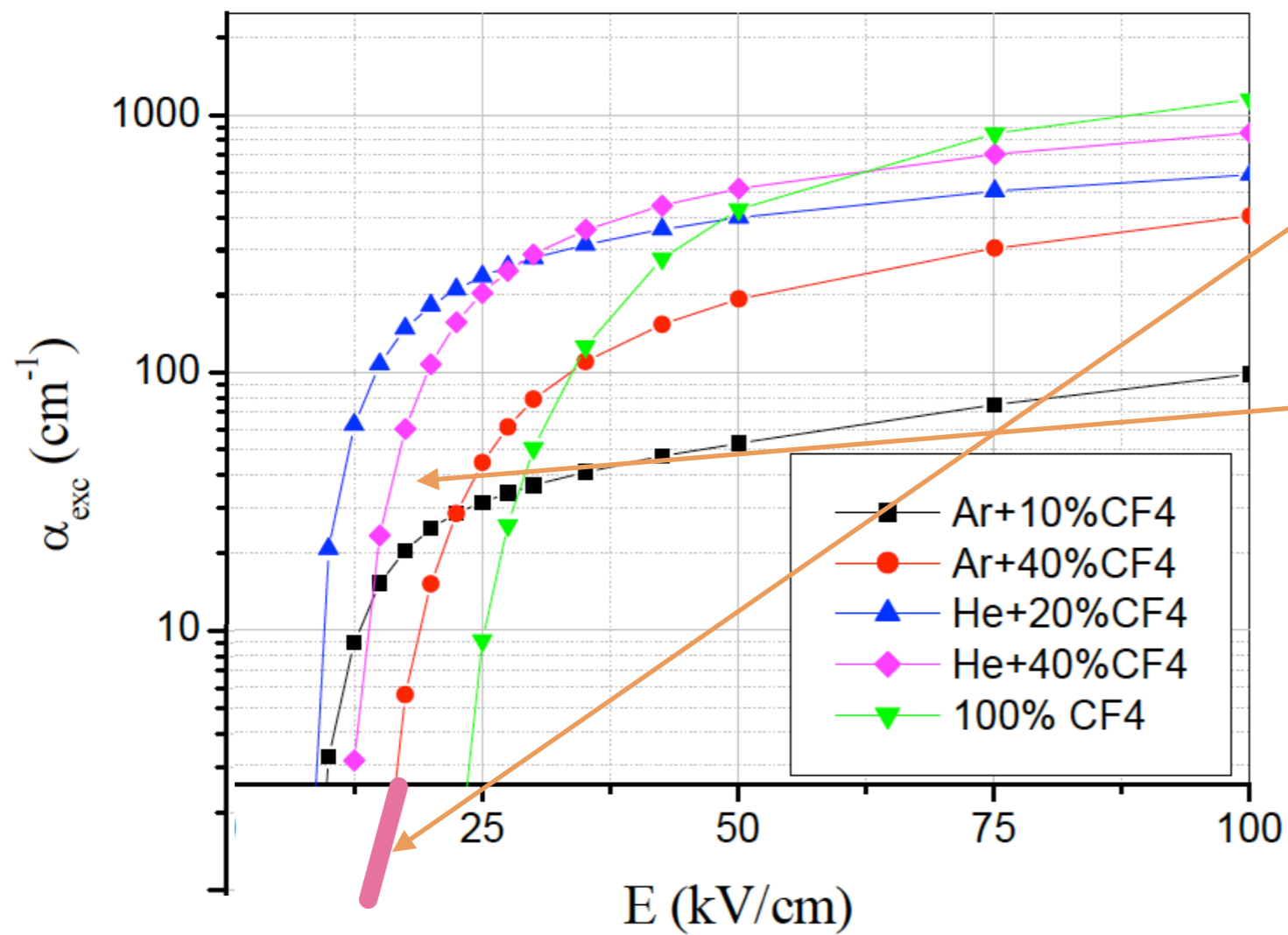
The light (mind the gap)



In order to get a light increase of a factor 2.5, a field of about 14 kV/cm is needed;

In the paper setup, with a V_{MESH} of 3400 V, we reached it with a gap of about 2.5 mm (in medium stat virtus)

The light



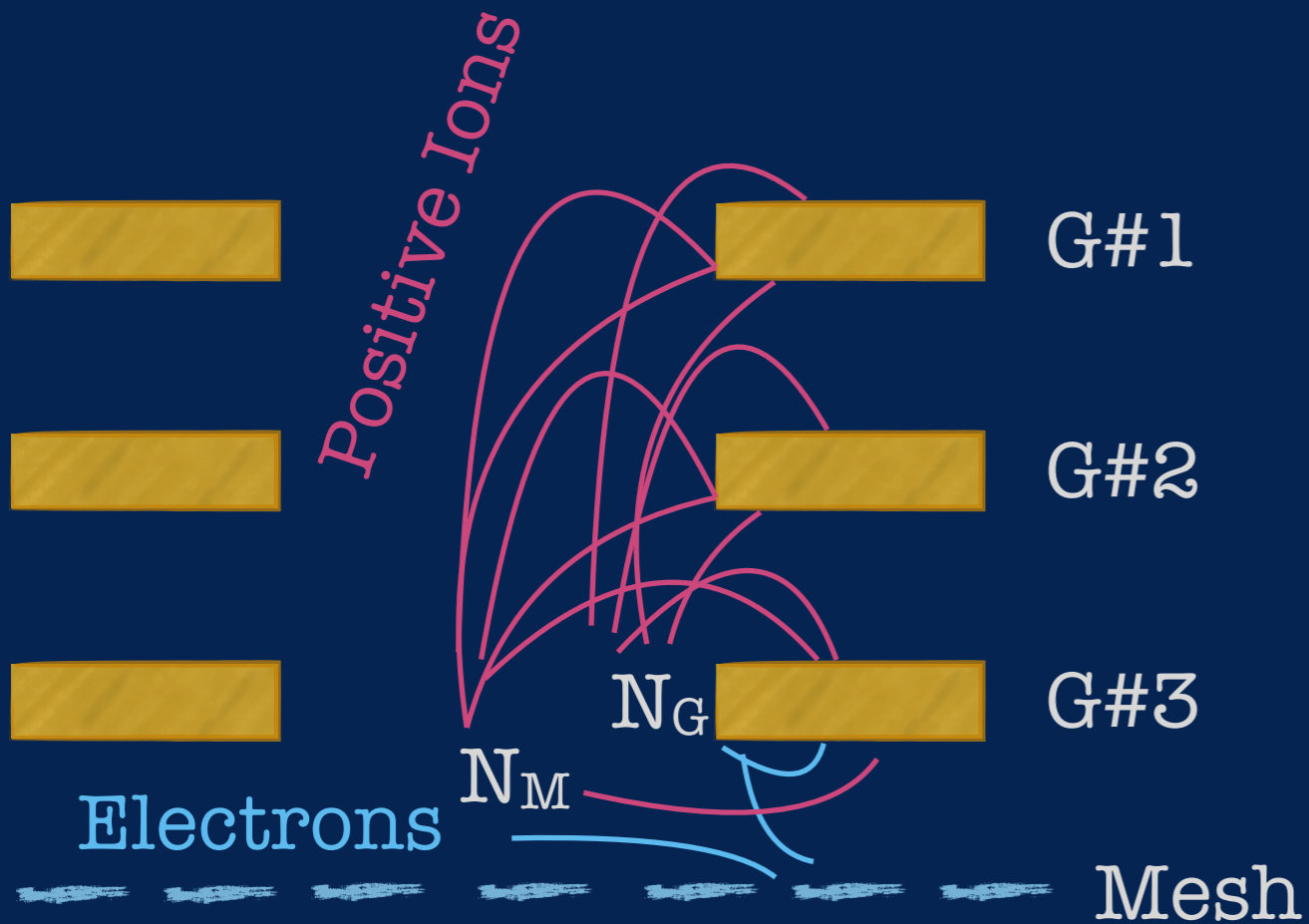
The increase of light production has a lower dependence on the Electric field than expected data do;

For high E values, produced photons are 10 times lower than expected;

I don't know how reliable the simulated values is;

Overall, our data are, at least, within the plot frame

The current



Let's assume all charges are produced in GEM#3 (N_G) and, in case, in the gap above the Mesh (N_M);

ϵ = electron extraction efficiency from GEM#3;

α = fraction of ions reaching GEM #1 and #2;

β = fraction of ions collected on GEM #3D;

$$I_{3D} = -(1 - \epsilon) \times N_G + \beta N_M$$

$$I_M = -\epsilon N_G - N_M$$

$$I_{3U} = (1 - \alpha)[N_G + (1 - \beta)N_M]$$

$$I_{21} = \alpha[N_G + (1 - \beta)N_M]$$

In general, we expect $\Sigma_{tot} = 0$

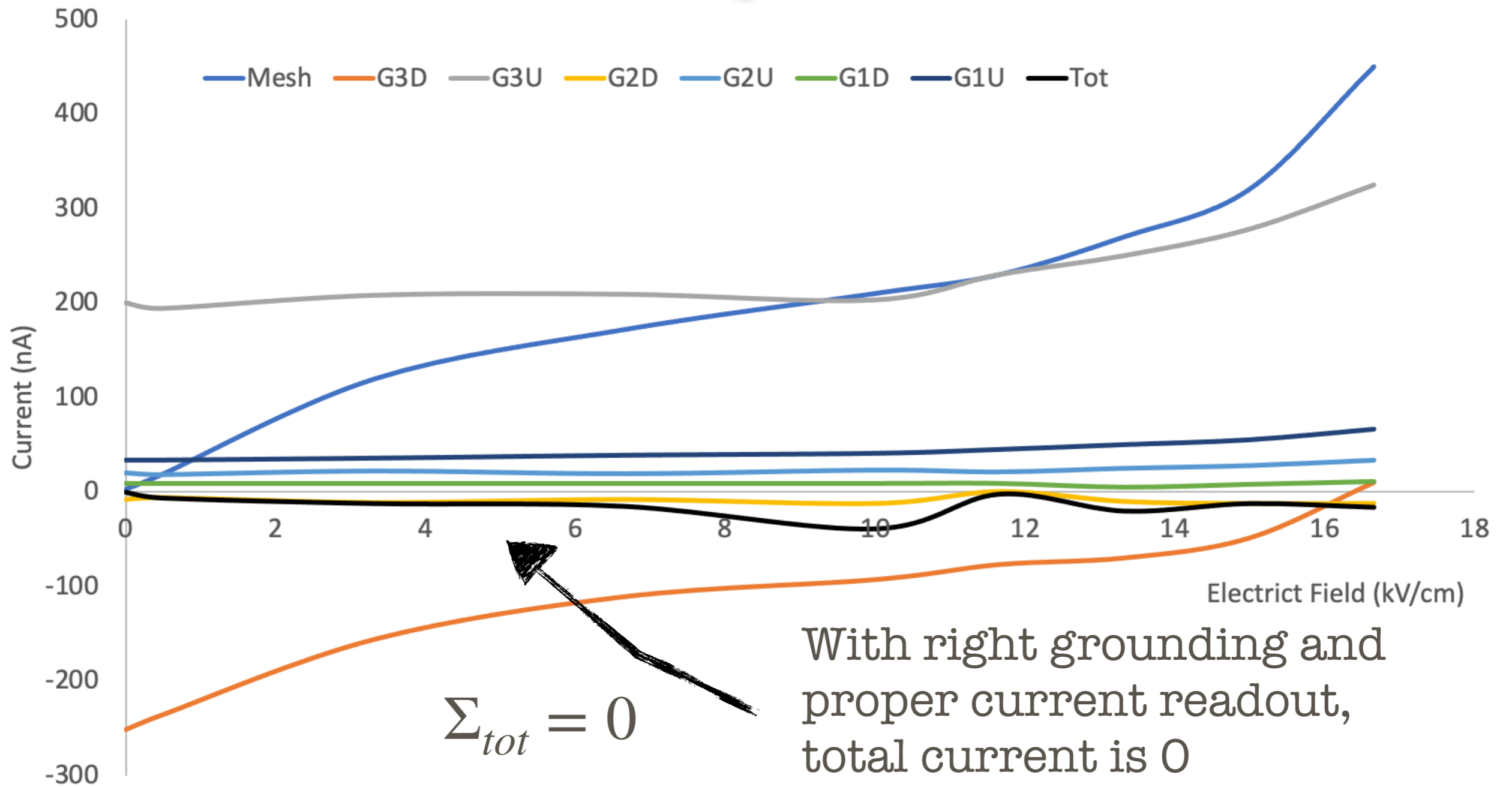
and in particular $I_M + I_{3D} = -(I_{3U} + I_{21})$

(equations are not independent)

$$\alpha = \frac{I_{21}}{I_{3U} + I_{21}}$$

If $N_M = 0$ (no gain because of the Mesh) $I_{3D} + I_M = -(I_{3U} + I_{21}) = -N_G$

The current



Simple model

Actually, N_G (if any) would depend on N_M :

$$N_M = \epsilon N_G \cdot e^{\alpha_T E_M} = \epsilon \delta N_G$$

α_T = Townsend coefficient

$\delta = e^{\alpha_T E_M}$ = gain in the gap below the G#3

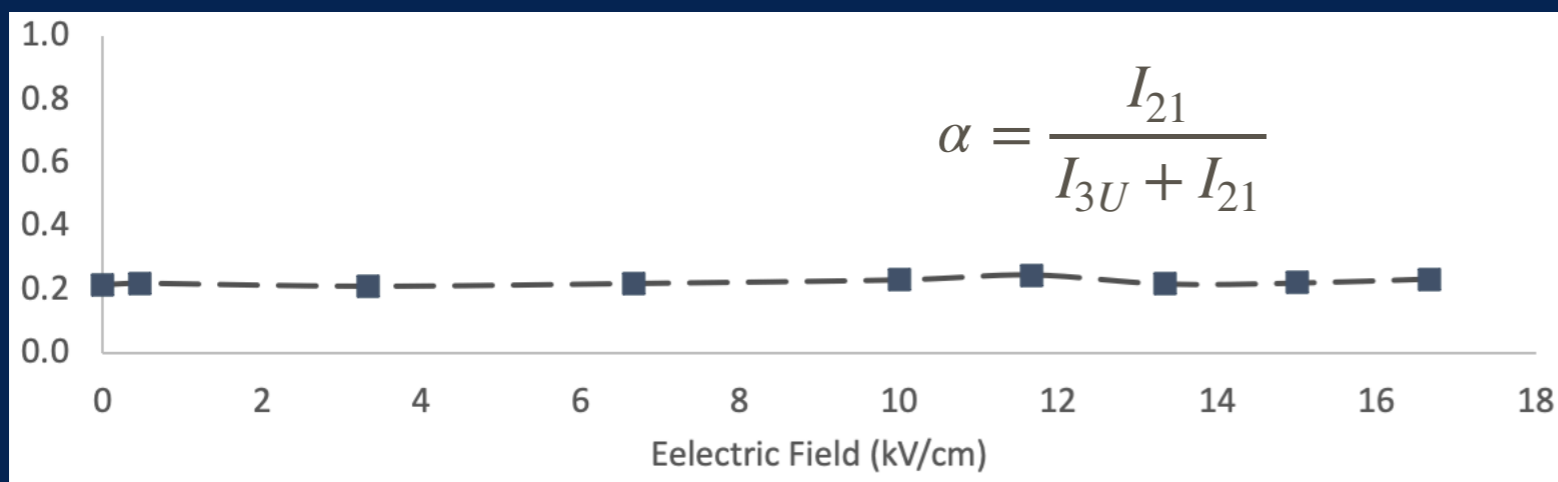
$$I_{3D} = [\beta \epsilon \delta - (1 - \epsilon)] N_G$$

$$I_M = -[\epsilon(1 + \delta)] N_G$$

$$A = I_{3U} + I_{21} = [1 + (1 - \beta)\epsilon\delta] N_G$$

$$I_{3D} + A = [1 + \delta]\epsilon N_G$$

$$I_{3D} + I_M = [\epsilon\delta(\beta - 1) - 1] N_G$$

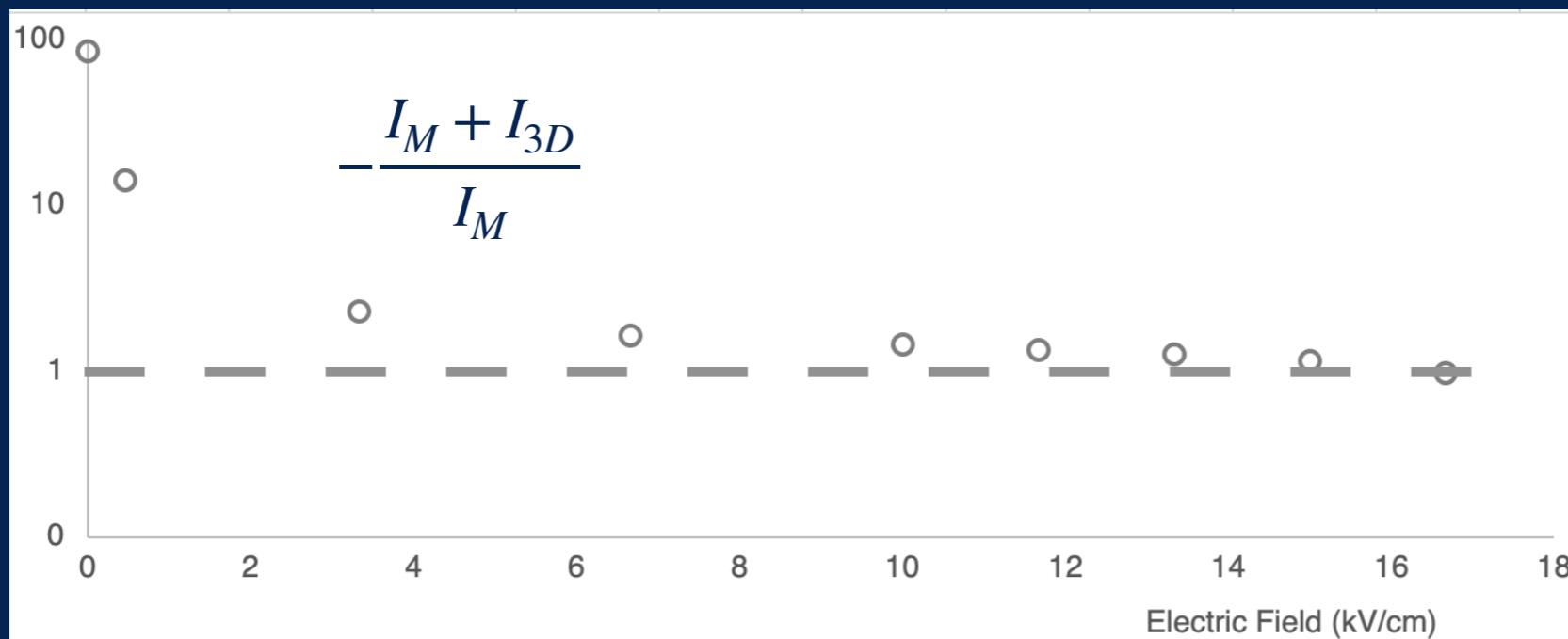


α = fraction of ions reaching GEM #1 and #2;

Simple model

Moreover: $I_M + I_{3D} = N_G[\epsilon\delta(\beta - 1) - 1]$ and $-\frac{I_M + I_{3D}}{I_M} = \frac{1 - \epsilon\delta(\beta - 1)}{1 + \delta}$

In case $E_M \rightarrow \infty$, then $-\frac{I_M + I_{3D}}{I_M} \rightarrow 1$ if $\beta \rightarrow 0$ and $\epsilon \rightarrow 1$



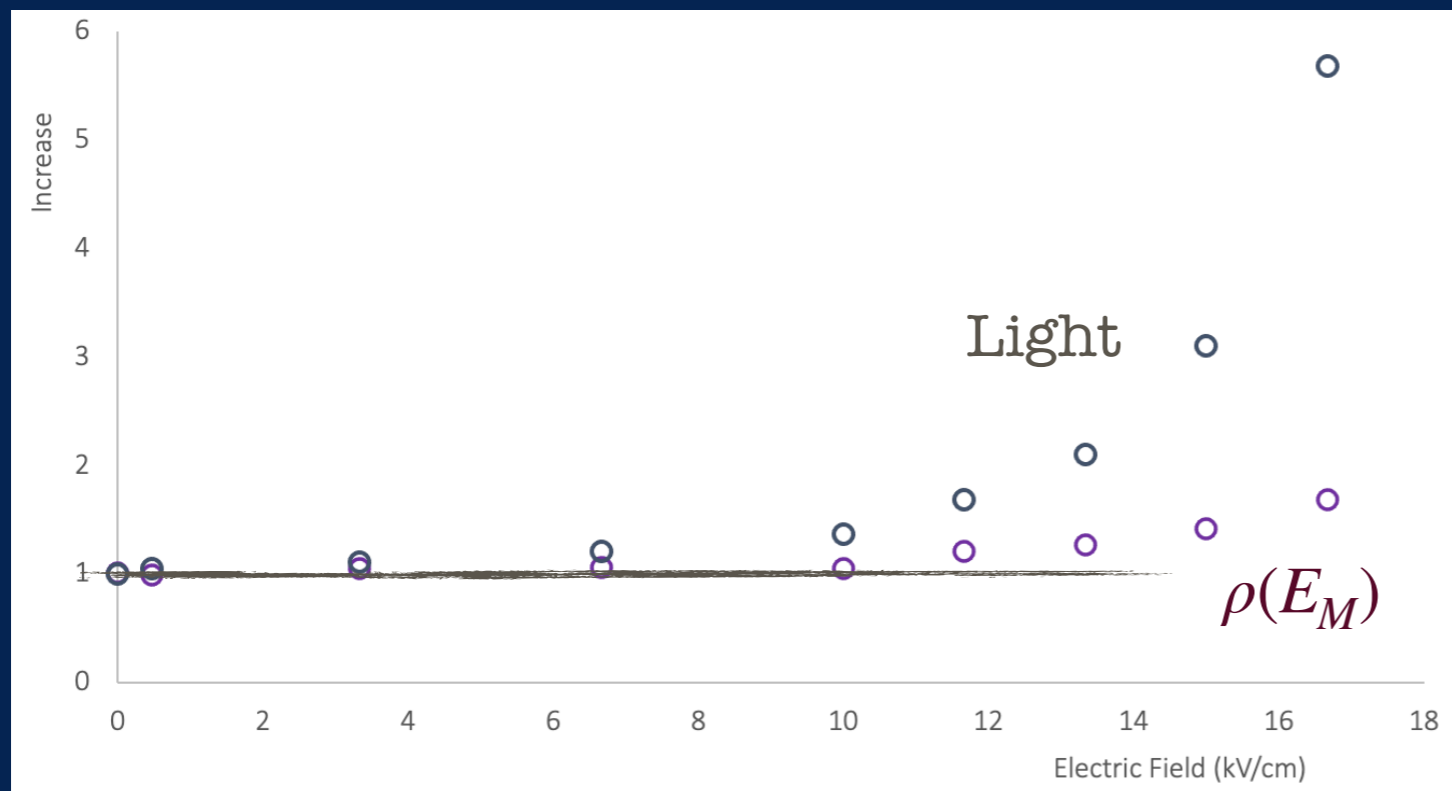
Are we allowed to suppose that for high fields $\beta = 0$ and $\epsilon = 1$?

Simple model

If we assume that at high E_M values $\epsilon = 1 \rightarrow$

$$\rho(E_M) = \frac{(I_{3D}(E_M) + I_M(E_M))}{I_{3D}^0} = \frac{N_G(E_M)[1 + \delta(E_M)]}{N_G^0}$$

Therefore, in the hypothesis $\epsilon = 1 \rightarrow \rho(E_M)$ will represent the total amount of electrons



For electric fields larger than 10 kV/cm, $\rho(E_M)$ starts to be significantly different from 1

Simple model (part 3)

Are we allowed to suppose that $\beta = 0$?

In this case

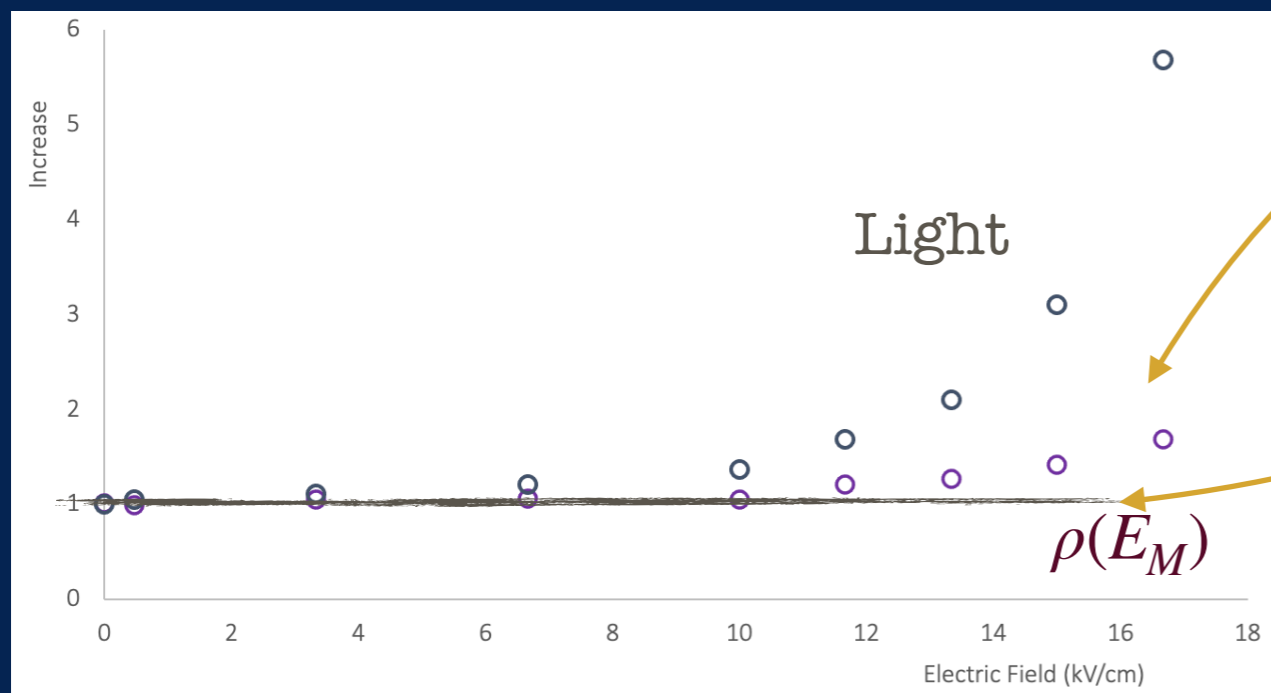
$$I_{3D} = [(\epsilon - 1)]N_G$$

$$I_M = -[\epsilon(1 + \delta)]N_G$$

$$A = I_{3U} + I_{21} = [1 + \epsilon\delta]N_G$$

$$I_{3D} + A = [1 + \delta]\epsilon N_G$$

$$I_{3D} + I_M = [\epsilon\delta - 1]N_G$$



$$\rho(E_M) = \frac{N_G(E_M)[1 + e^{\alpha_T E_M}]}{N_G^0}$$



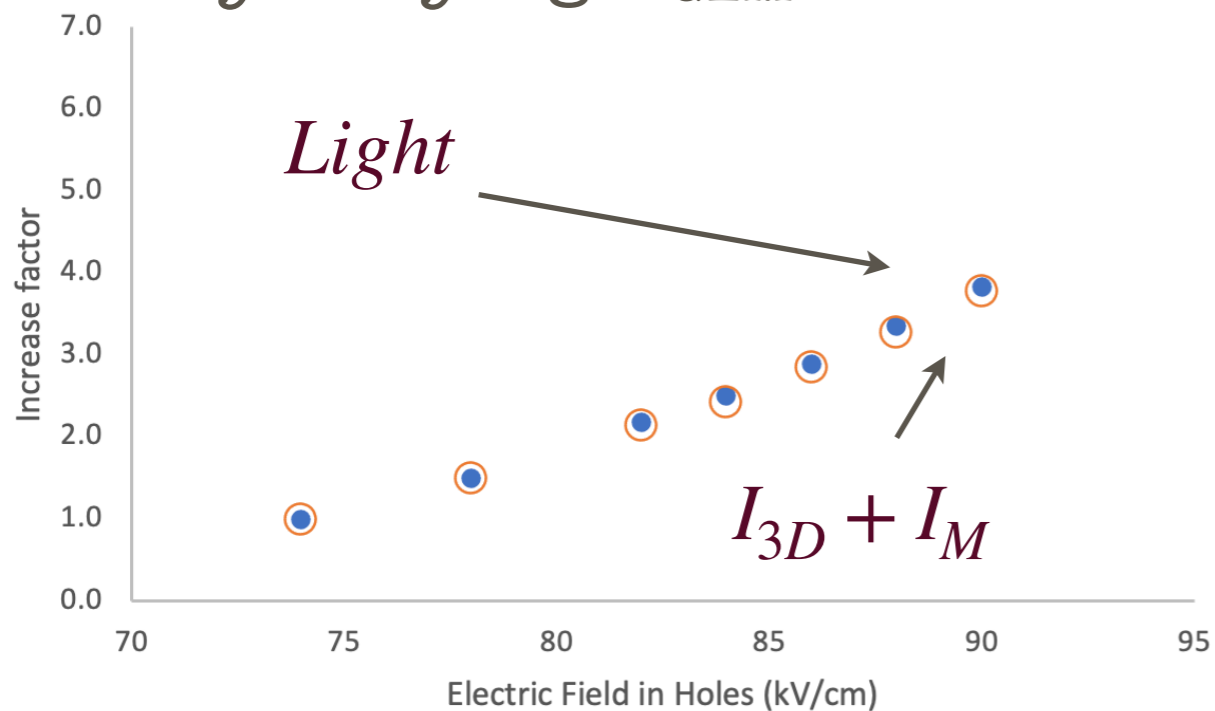
GEM#3 Electric field in the holes can be evaluated as

Mesh

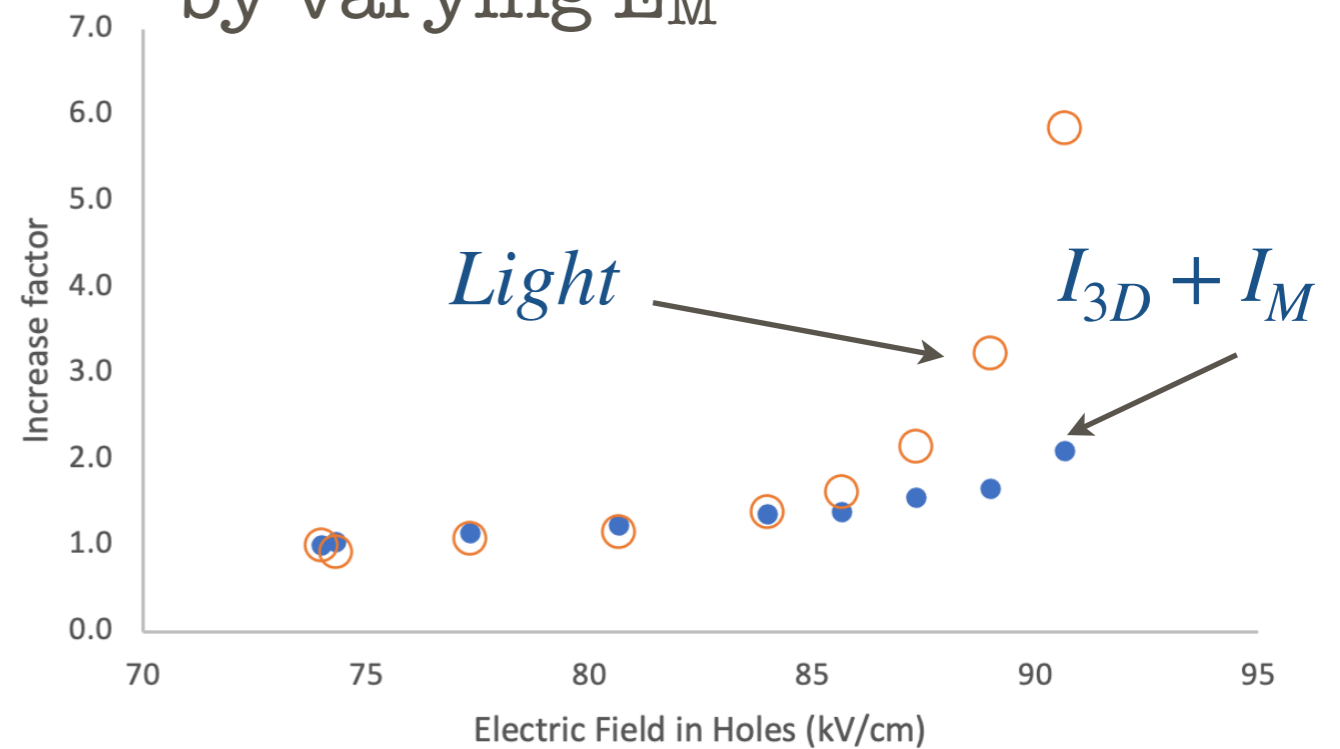
$$E_h = \frac{V_{GEM}}{50\mu m} + E_M$$

We studied the behavior of light and current as a function E_h ;

by varying V_{GEM}



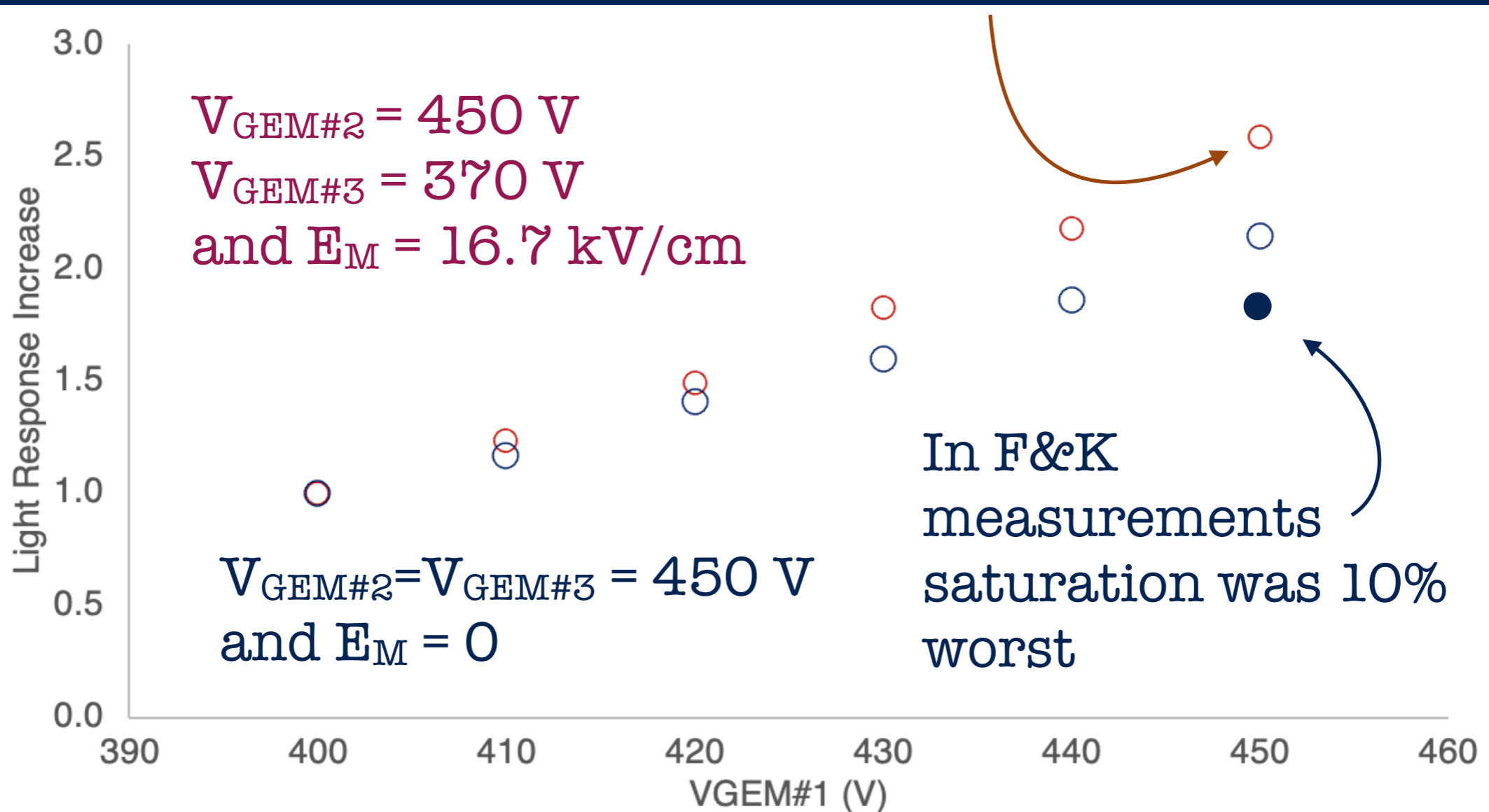
by varying E_M



When increasing V_{GEM} light and current have the same behavior;
Effect of the E_M seems completely different;

Saturation?

According to F&K measurements,
expected value was 2.5



Conclusion

Results with flat mesh and better understanding of HV grounding scheme seem to be solid and reliable:

- A light increase of a factor 5-6 was observed;
- A concurrent 1.7 increase in charge was visible;
- Preliminary analysis indicates this to be due gain in the gap between GEM and MESH;
- The difference between light and charge confirms a light production induced by non-ionizing (or very low-ionizing) electrons.